

Fig. 1

200220" 6266200T

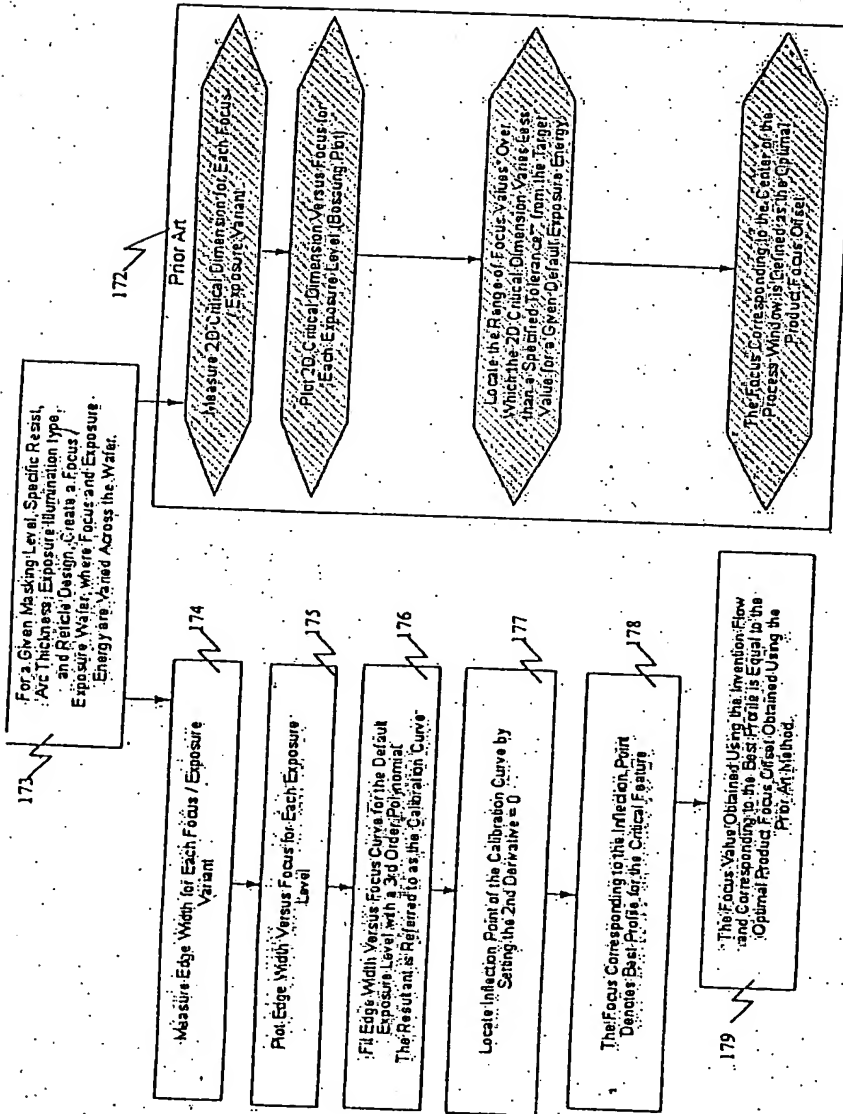


Fig. 1A

20022016262001

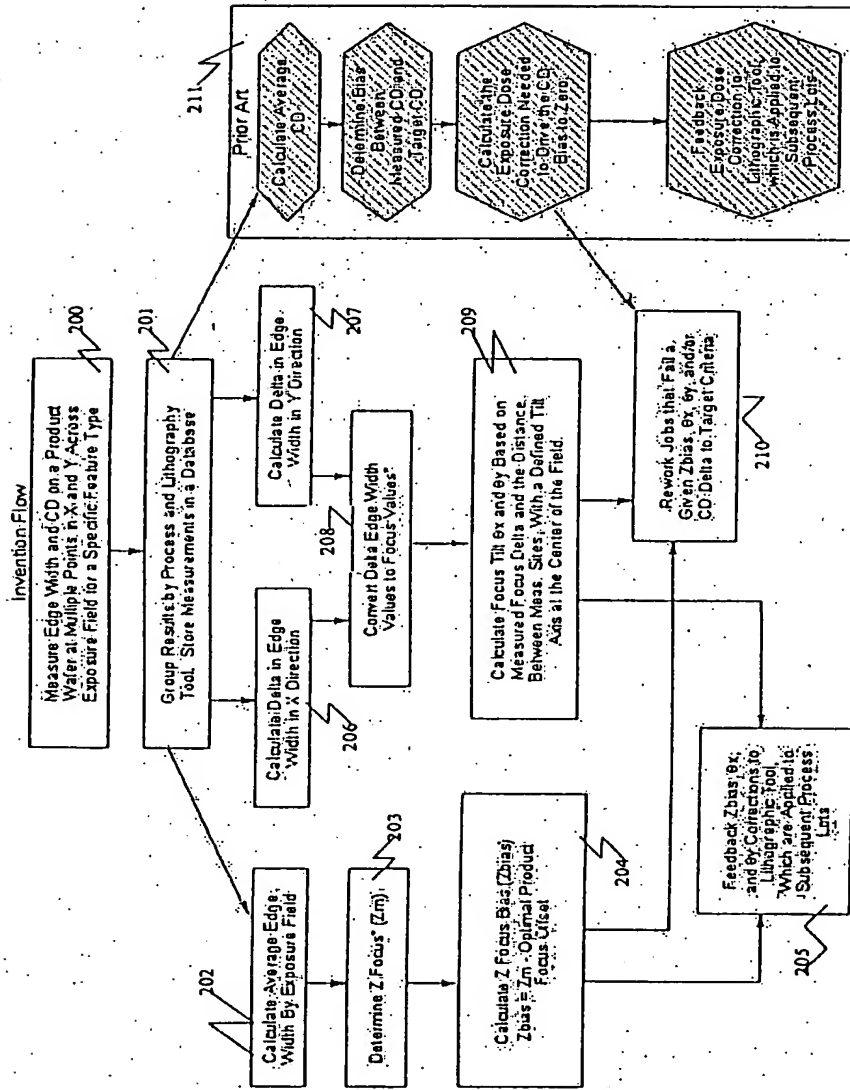
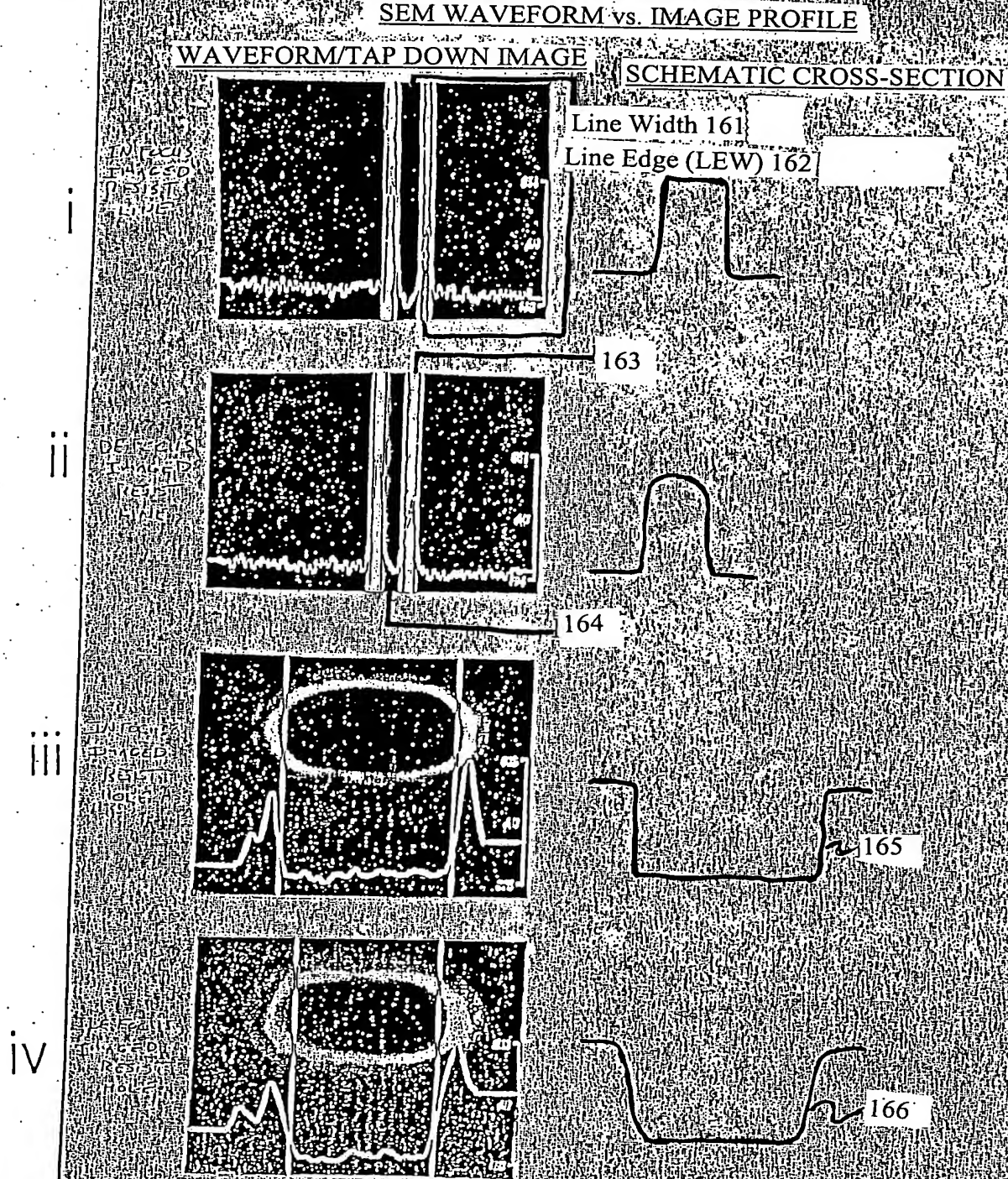


Fig. 1B

10079389 022002



200220" 62E6/00F

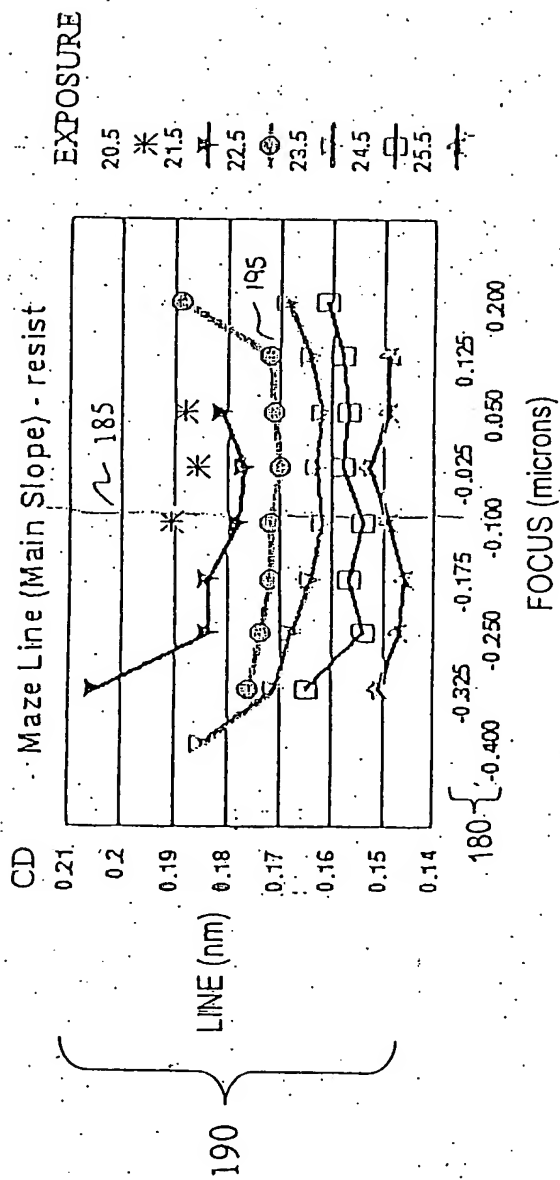


Fig. 1D

200220" 68E6Z00T

Resist Contact Dimension Change With Focus and/or Exposure
KCELL Contacts (Bottom View) - Resist

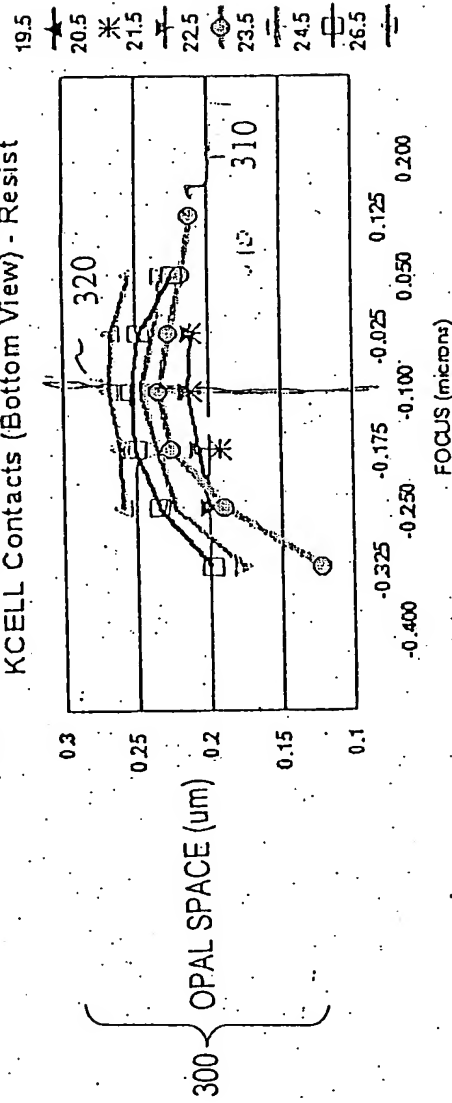


Fig. 2

200220"68E6Z001

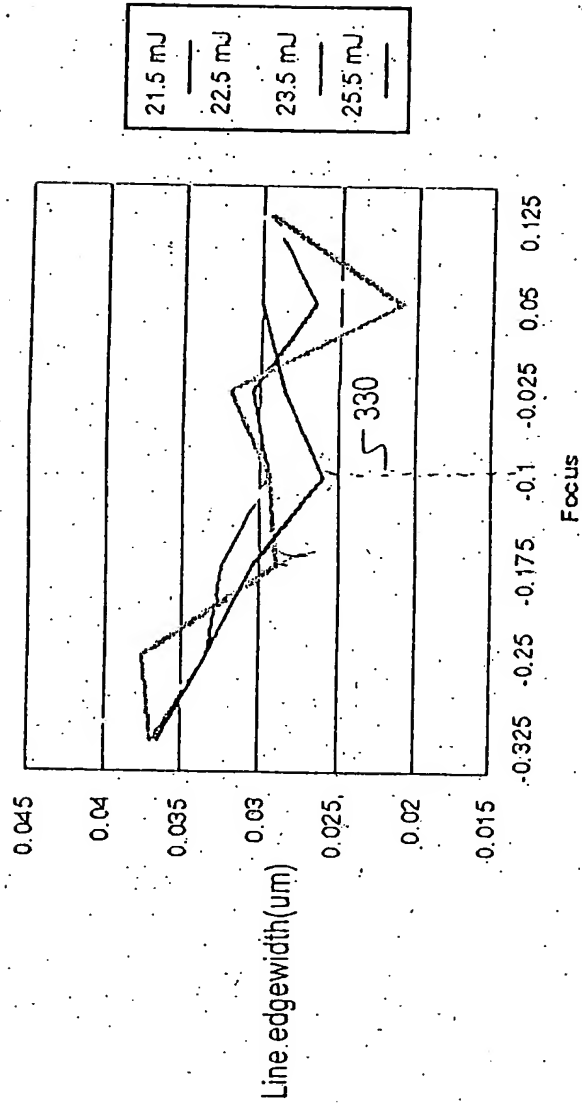


Fig 3

200220 68262001

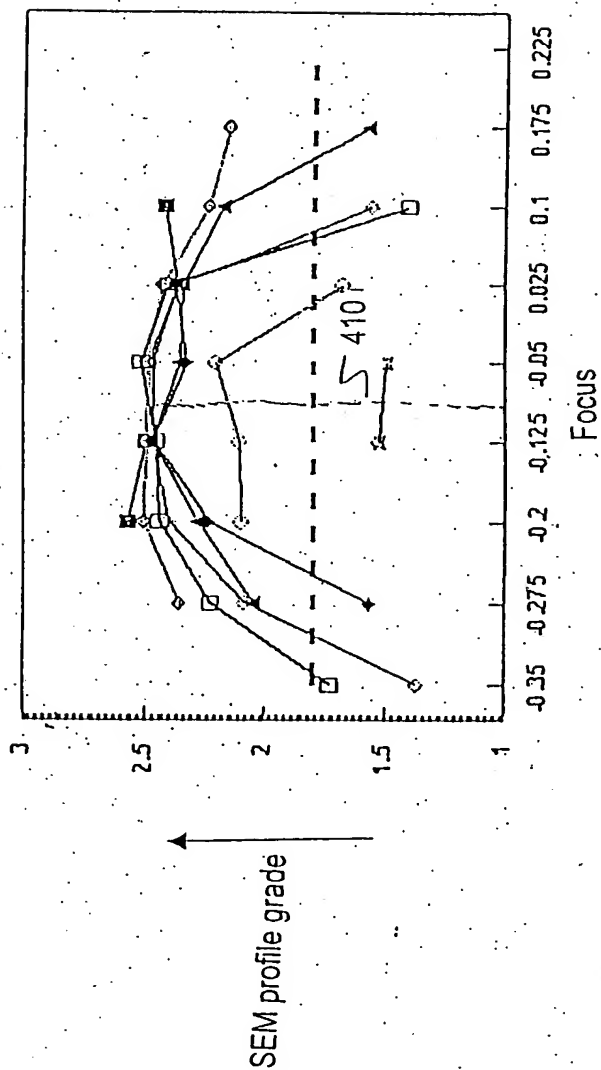


Fig. 4

2003220 68262001

Critical Dimension of Imaged Photoresist as Measured by CD

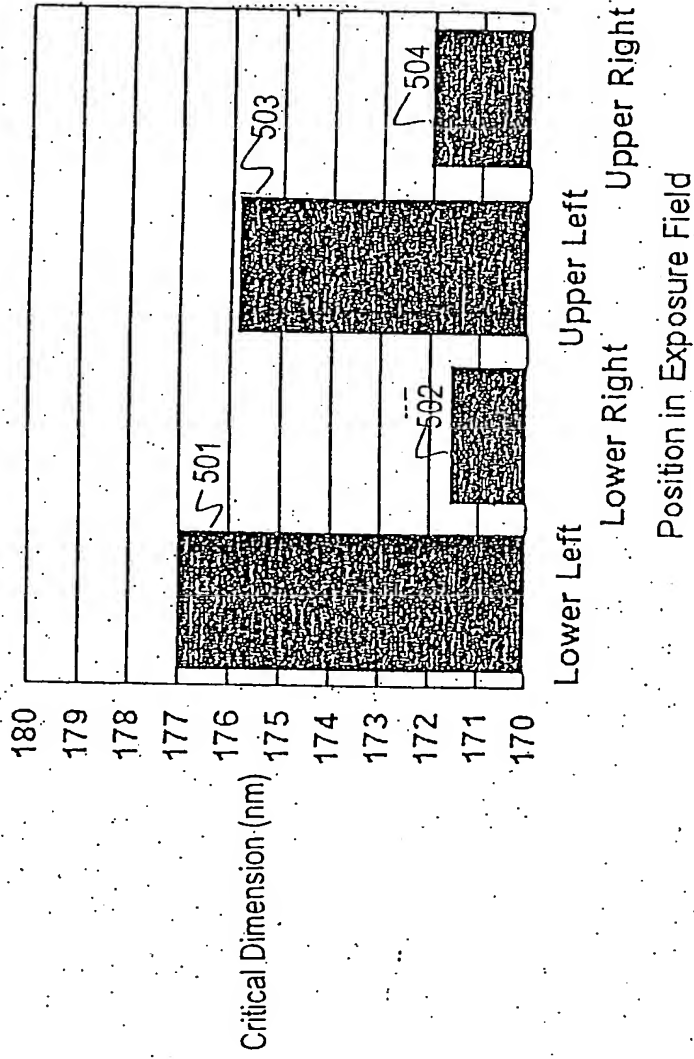


Fig. 5

200220" 6226/001

Line Edge Width of Imaged Photoresist as Measured by CD

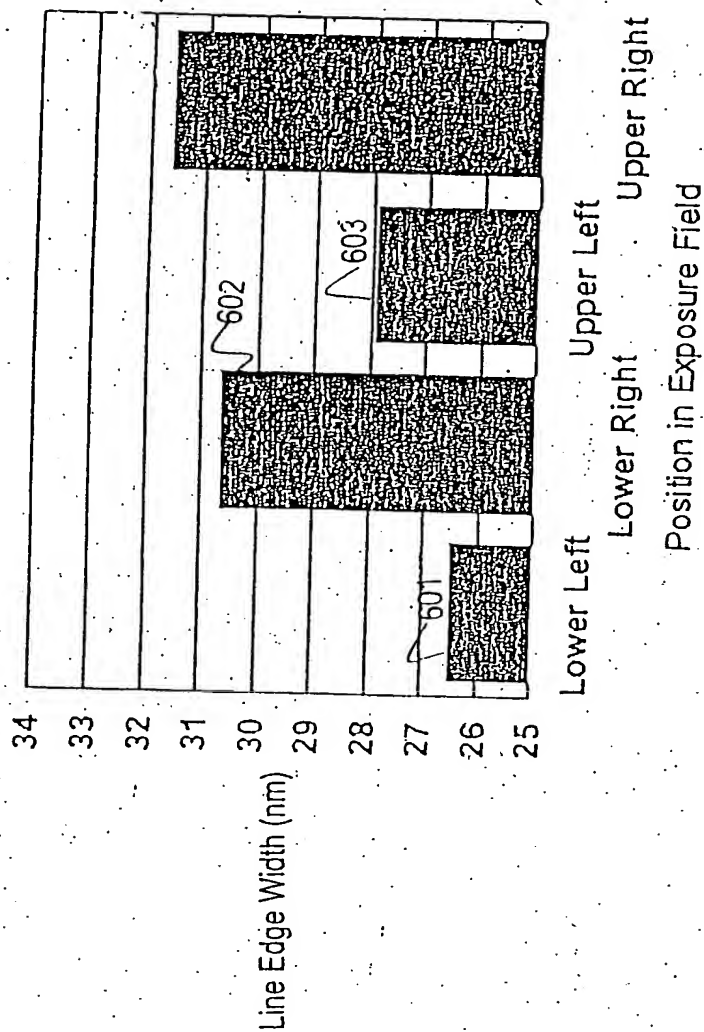


Fig. 6

200220* 68662001

XY Tilt Determination Using Edge Width Measurement



Fig. 7

200229 68262001

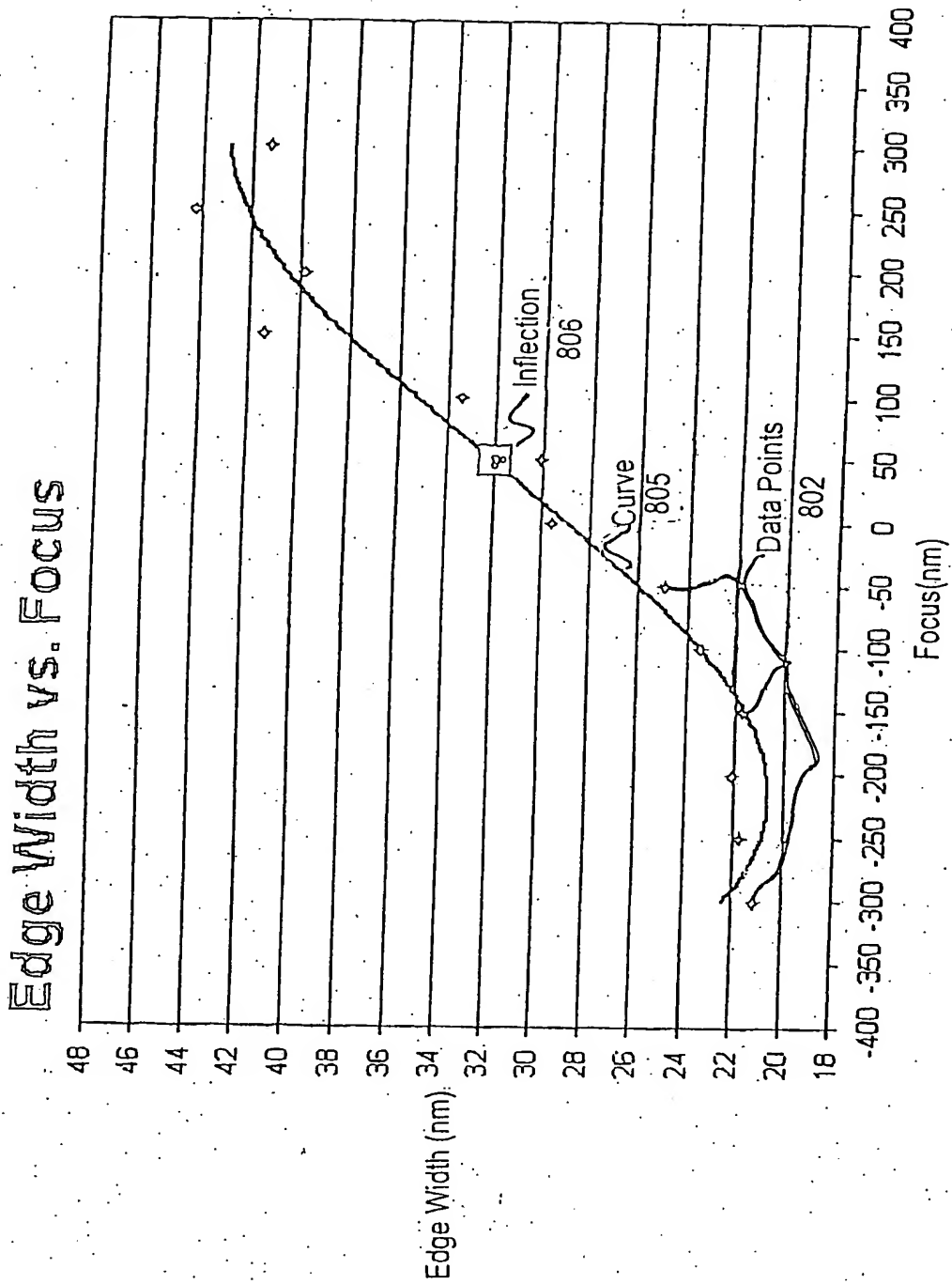


Fig. 8

20010128US1

XY Tilt Determination Using Edge Width Measurement

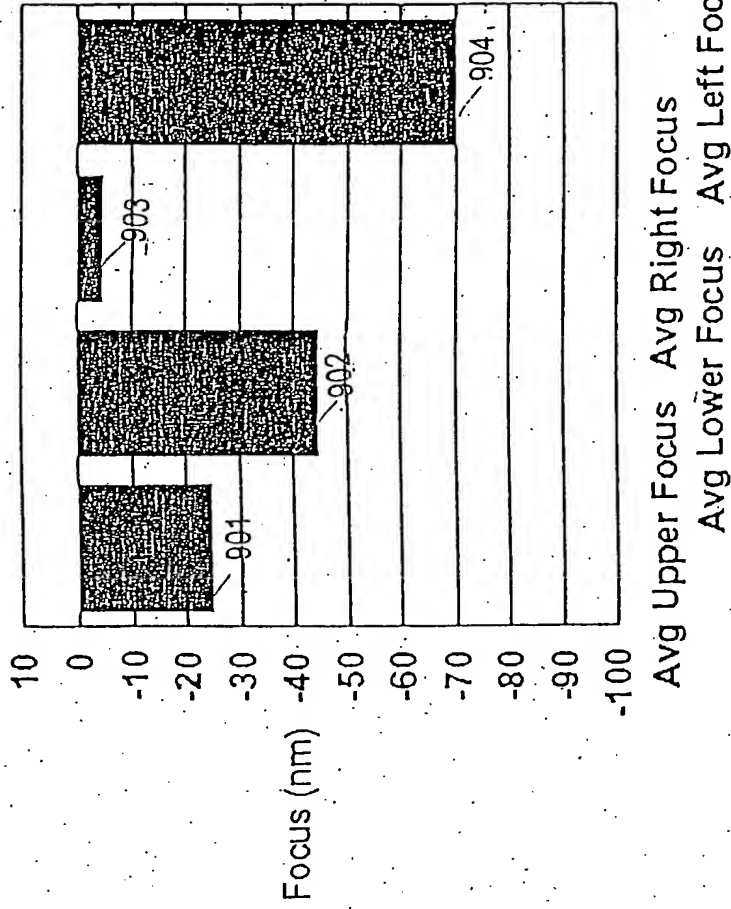


Fig. 9

2022 082200F

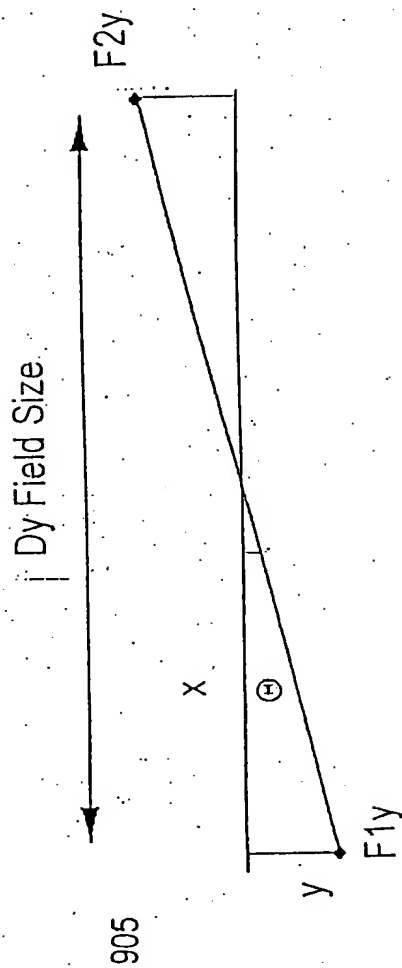


Fig. 10

Tool Check Center of Focus vs Atmospheric Press

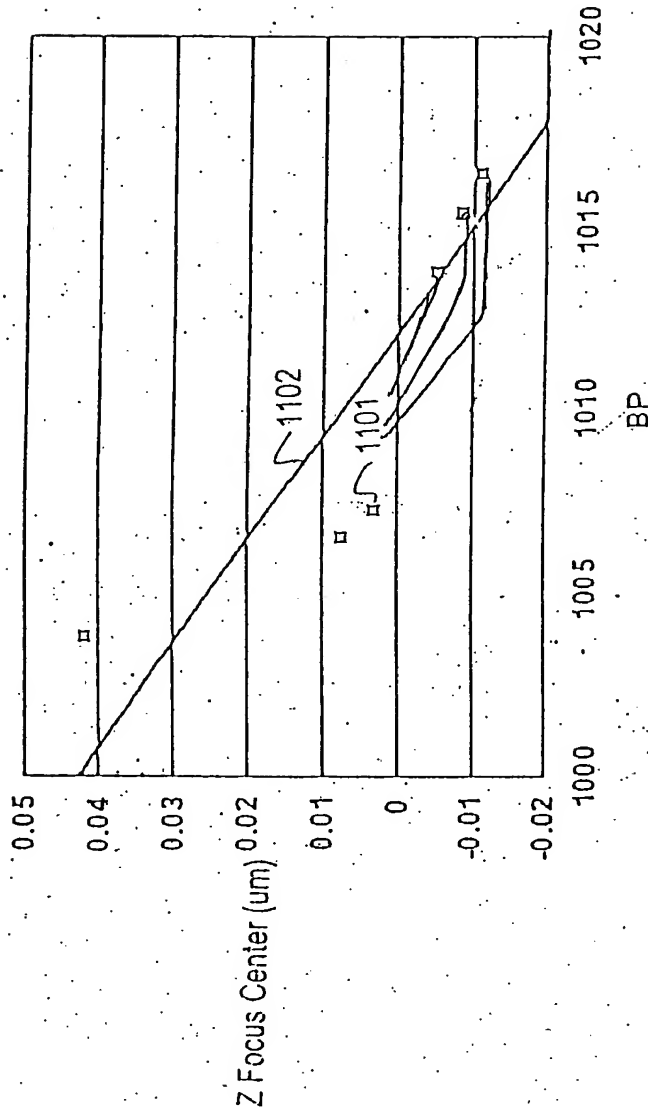


Fig. 11

20020" 68E6'001

Edge Width vs Atmospheric Pressure

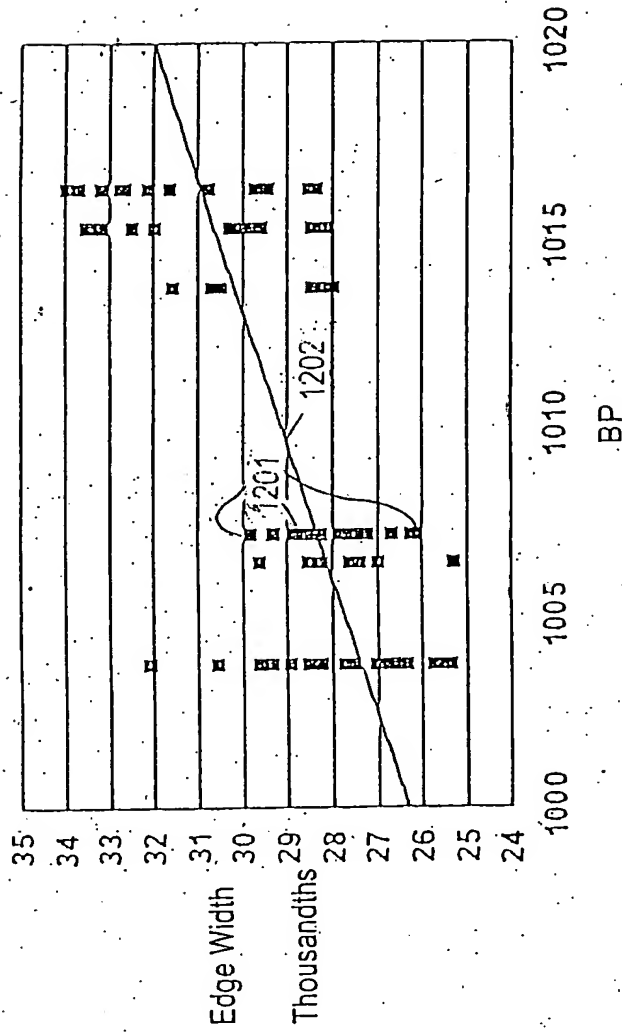


Fig. 12

TABLE OF RUN RULES

1310 Tool	1320 Technology	1330 WaferPN	1340 Process	1350 Opt	1360 Default Exposure	1370 Focus
U82V	ICE8S3D	*	MC	F	19.00	0.10
U82V	ICEC8S2	*	MC	F	19.00	0.10
U82V	ICEC8S3	*	MC	F	19.00	0.10
U84V	CM0S6X1	*	MC	F	20.00	0.00
U86V	CS0I9S0	*	MC9S	F	24.00	-0.10
U86V	CS0I9S0	0000008J0640	MC9S	F	30.00	-0.10
U86V	CS0I9S0	0000008J0645	MC9S	F	30.00	-0.10
U86V	CS0I9S0	0000057P6438	MC9S	F	28.00	-0.05
U86V	CS0I9S2	*	MC9S	F	25.00	-0.10
U92V	CS0I9S0	*	MC9S	F	24	-0.10
U92V	CS0I9S0	0000008J0639	MC9S	F	30.00	-0.10
U92V	CS0I9S0	0000008J0640	MC9S	F	30.00	-0.10

Fig. 13 (Prior Art)

200220 6864001

200209*68E6200T

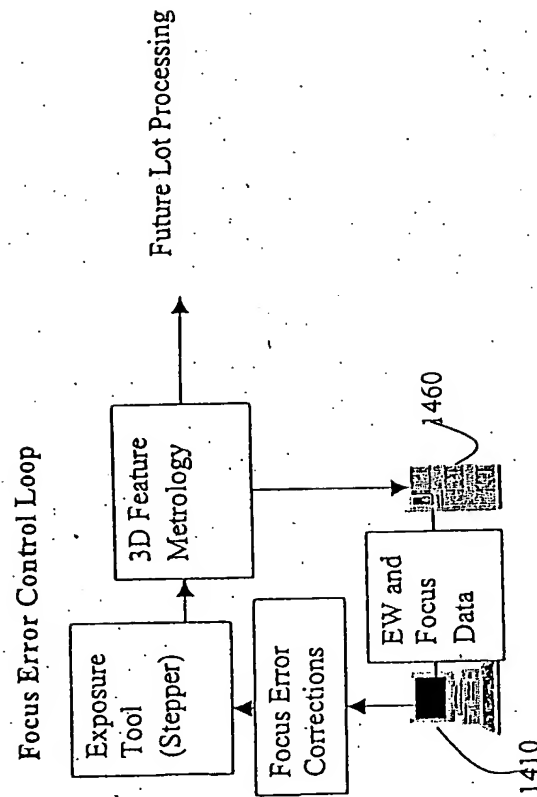


Fig. 14